



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Application of: **IRINO, Kiyoshi**

Serial No.: 09/428,052

Filed: **October 27, 1999**

#18/F
6/5/02
Group Art Unit 2815

Examiner: *Smith*
Jose R. Diaz

P.T.O. Confirmation No.: 4139

FOR: SEMICONDUCTOR MEMORY DEVICE CONTAINING NITROGEN IN A GATE OXIDE FILM

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

June 3, 2002

Sir:

In response to the Office Action dated **March 1, 2002**, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 13 without prejudice or disclaimer.

Please amend claims 6 and 10 as follows:

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6. (Four Times Amended) A method of fabricating a semiconductor device, comprising the steps of:

forming a gate oxide film on a substrate by a thermal oxide film;

forming a gate electrode pattern on said gate oxide film;

forming diffusion regions in said substrate at both lateral sides of said gate electrode pattern by introducing an impurity element into said substrate through said gate oxide film while using said gate electrode pattern as a mask; and

introducing N atoms into said gate oxide film while using said gate electrode pattern as a

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